

FQPF9N50CF N-Channel QFET® FRFET® MOSFET

500 V, 9 A, 850 mΩ

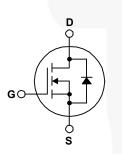
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and • Fast Recovery Body Diode (Typ. 100 ns) electronic lamp ballasts.

Features

- 9 A, 500 V, R_{DS(on)} = 850 mΩ (Max.) @ V_{GS} = 10 V, I_D = 4.5 A
- Low Gate Charge (Typ. 28 nC)
- Low Crss (Typ. 24 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQPF9N50CF	Unit	
V _{DSS}	Drain-Source Voltage		500	V	
I _D	Drain Current - Continuous ($T_c = 25^{\circ}C$)		9*	А	
	- Continuous (T _C = 100°C)		5.4*	А	
I _{DM}	Drain Current - Pulsed	(Note 1)	36*	A	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	360	mJ	
I _{AR}	Avalanche Current	(Note 1)	9	А	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	4.4	mJ	
dv/dt	Peak Diode Recovery dv/dt (Not		4.5	V/ns	
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		44	W	
	- Derate above 25°C		0.35	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		300	°C	

* Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQPF9N50CF	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	2.86	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction to Ambient, Max.	62.5	°C/VV	

December 2013

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF9N50CF	FQPF9N50CF	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics			Į	Į	4
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I _D = 250 μ A	500			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, Referenced to 25°C		0.57		V/°C
I _{DSS} Zero (Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V			10	μA
		V _{DS} = 400 V, T _C = 125°C			100	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2.0		4.0	
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 4.5 A		0.70	0.85	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 4.5 A		6.5		S
Dynamic C	haracteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 V, V_{GS} = 0 V,$		790	1030	p₽
C _{oss}	Output Capacitance	f = 1.0 MHz		130	170	pF
C _{rss}	Reverse Transfer Capacitance			24	30	pF
Switching (Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250 V, I _D = 9A,		18	45	ns
t _r	Turn-On Rise Time	$R_{G} = 25 \Omega$		65	140	ns
t _{d(off)}	Turn-Off Delay Time			93	195	ns
t _f	Turn-Off Fall Time	(Note 4)		64	125	ns
Qg	Total Gate Charge	V _{DS} = 400 V, I _D = 9A,		28	35	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	-	4		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	7	15		nC
Drain-Sour	ce Diode Characteristics and Maximum Ratings	5			1	
I _S	Maximum Continuous Drain-Source Diode Forward Current				9*	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				36*	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 9 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 9 A,		100	-	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		0.3		μC

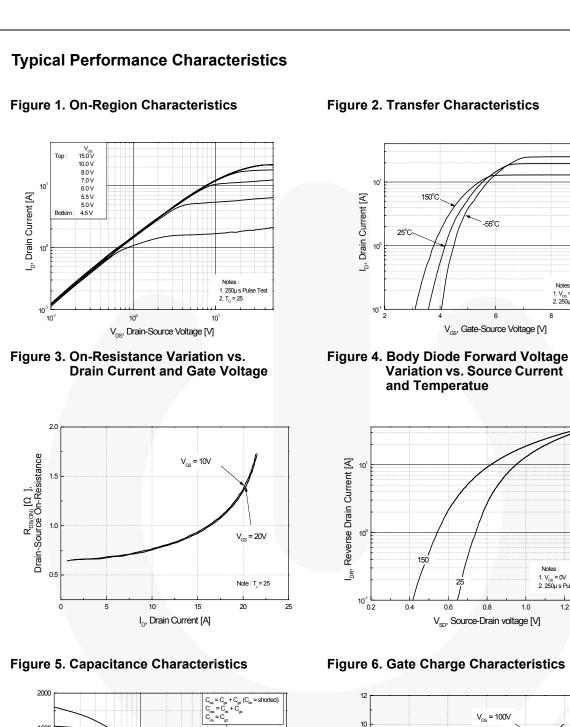
NOTES:

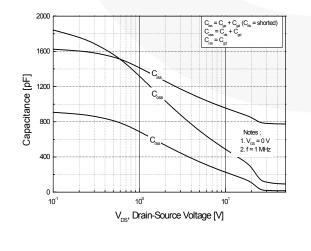
1. Repetitive rating : pulse-width limited by maximum junction temperature.

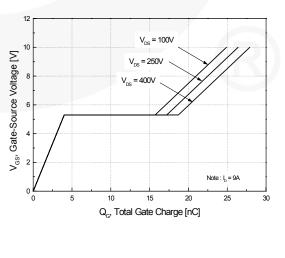
2. L = 8 mH, I_{AS} = 9 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.

3. I_{SD} \leq 11 A, di/dt \leq 200 A/µs, V_{DD} \leq BV_{DSS,} Starting ~T_J = 25°C.

4. Essentially independent of operating temperature.







0.8

-55°C

Notes : 1. V_{DS} = 40V 2. 250µ s Pulse Test

10

8

Notes :

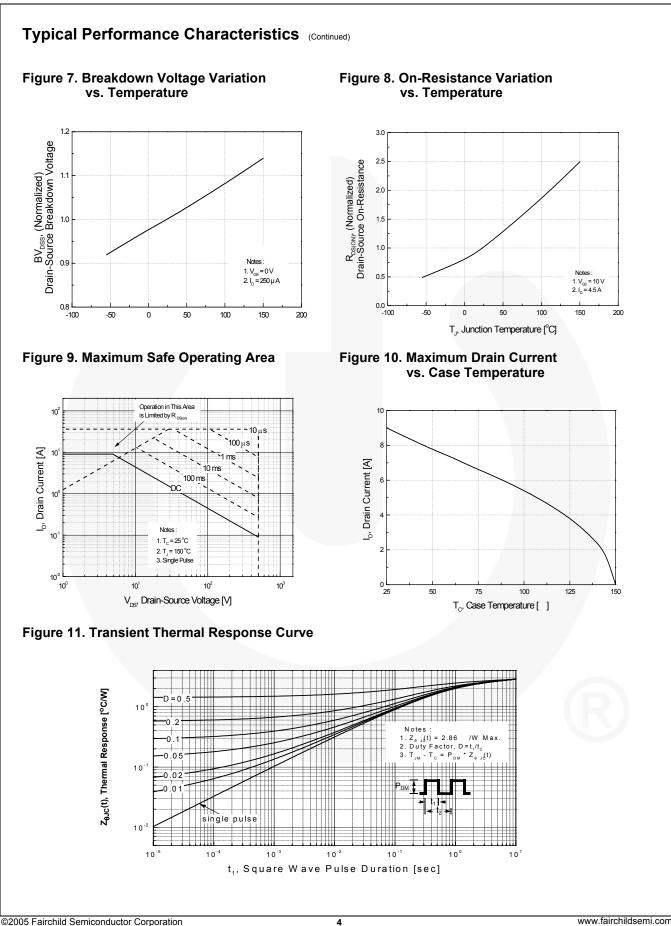
1.0

1. V_{GS} = 0V 2. 250µ s Pulse Test

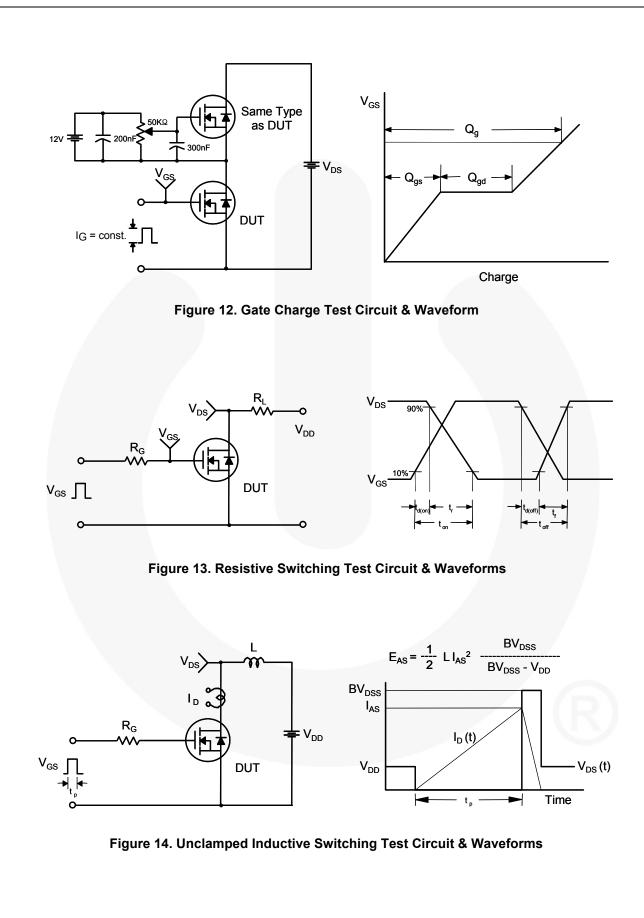
1.2

1.4

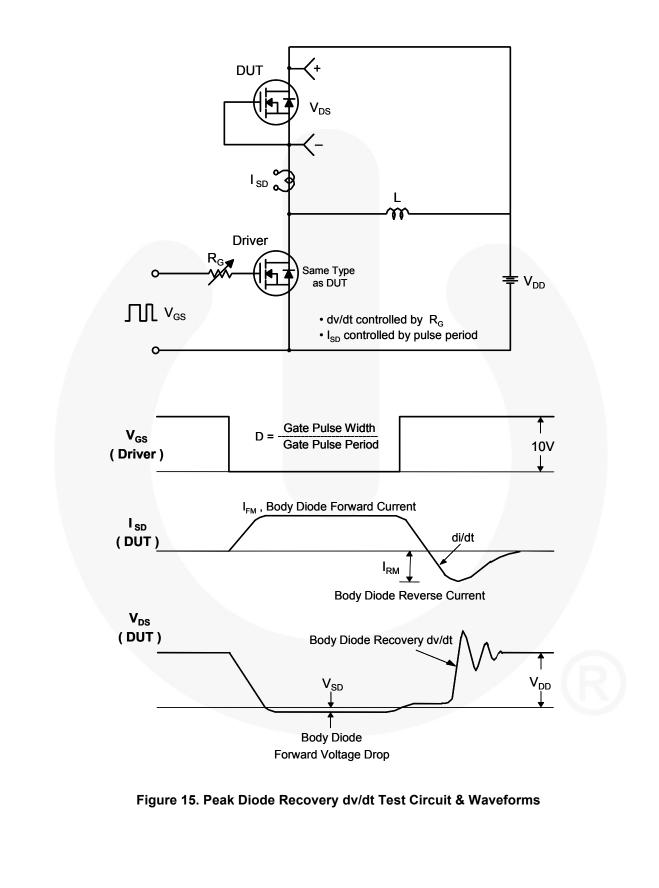
©2005 Fairchild Semiconductor Corporation FQPF9N50CF Rev C1

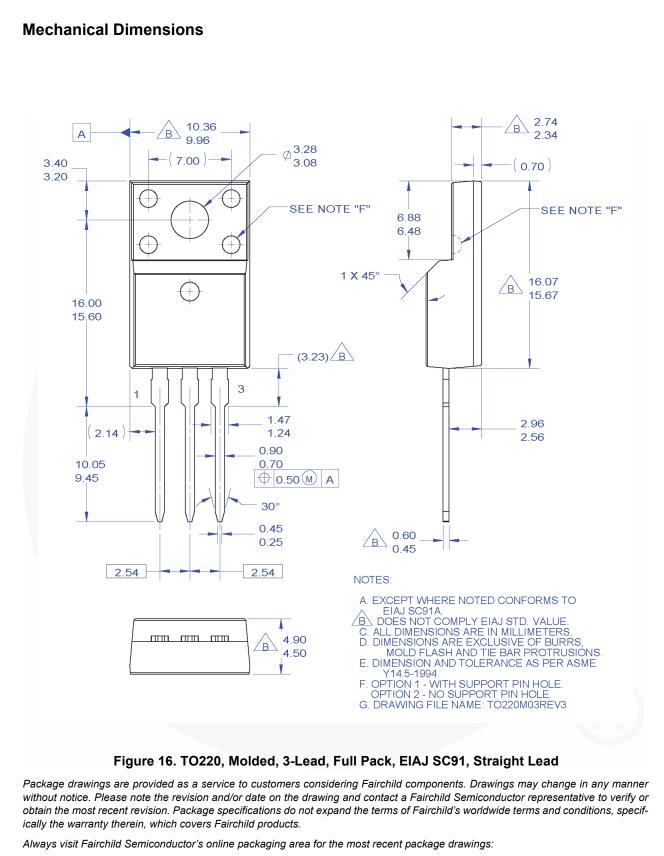


4



FQPF9N50CF — N-Channel QFET® FRFET® MOSFET





http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TF220-003

FQPF9N50CF — N-Channel QFET[®] FRFET[®] MOSFET



SEMICONDUCTOR

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™	F-PFS™	
AX-CAP [®] *	FRFET®	
BitSiC™	Global Power Resource SM	PowerTrench [®]
Build it Now™	GreenBridge™	PowerXS™
CorePLUS™	Green FPS™	Programmable Active Droop™
CorePOWER™	Green FPS™ e-Series™	QFET®
CROSSVOLT™	Gmax™	QS™
CTL™	GTO™	Quiet Series™
Current Transfer Logic™	IntelliMAX™	RapidConfigure™
DEUXPEED®	ISOPLANAR™	
Dual Cool™	Marking Small Speakers Sound Louder	
EcoSPARK®	and Better™	Saving our world, 1mW/W/kW at a time™
EfficentMax™	MegaBuck™ Micescolupi Ep.™	SignalWise™
ESBC™	MICROCOUPLER™	SmartMax™
R	MicroFET™ Micro Dela™	SMART START™
	MicroPak™ MicroPak2™	Solutions for Your Success™ SPM [®]
Fairchild®	MillerDrive™	SFM [™] STEALTH™
Fairchild Semiconductor®	MotionMax™	SuperFET®
FACT Quiet Series™ FACT [®]	mWSaver®	SuperSOT™-3
FACT [®]	OptoHiT™	SuperSOT™-6
FAST ⁻ FastvCore™	OPTOLOGIC®	SuperSOT™-8
FETBench™	OPTOPLANAR®	SupreMOS [®]
FPS™		SyncFET™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

Sync-Lock™ SYSTEM^{®*} GENERAL

TinyBoost[®]

TinyBuck® TinyCalc™ TinvLogic® TINYOPTO™

TinvPower™ TinyPWM™

TinyWire™

TranSiC™

UHC® Ultra FRFET™

VCX™

XS™

UniFFT™

VisualMax™

VoltagePlus™

TriFault Detect™

TRUECURRENT®* μSerDes™

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor: